

## General Description

CMSV65R190Q is power MOSFET using Cmos's advanced super junction technology that can realize very low on-resistance and gate charge. It will provide much high efficiency by using optimized charge coupling technology. These user friendly devices give an advantage of Low EMI to designers as well as low switching loss.

## Features

- Fast switching
- 100% avalanche tested
- RoHS Compliant

## Absolute Maximum Ratings

| Symbol                 | Parameter                              | Rating     | Units |
|------------------------|----------------------------------------|------------|-------|
| $V_{DS}$               | Drain-Source Voltage                   | 650        | V     |
| $V_{GS}$               | Gate-Source Voltage                    | ±30        | V     |
| $I_D@T_C=25^{\circ}C$  | Continuous Drain Current               | 20         | A     |
| $I_D@T_C=100^{\circ}C$ | Continuous Drain Current               | 12         | A     |
| $I_{DM}$               | Pulsed Drain Current                   | 80         | A     |
| EAS                    | Single Pulse Avalanche Energy (Note 1) | 605        | mJ    |
| $P_D@T_C=25^{\circ}C$  | Total Power Dissipation                | 140        | W     |
| $T_{STG}$              | Storage Temperature Range              | -55 to 150 | °C    |
| $T_J$                  | Operating Junction Temperature Range   | -55 to 150 | °C    |

## Thermal Data

| Symbol          | Parameter                           | Typ. | Max. | Unit |
|-----------------|-------------------------------------|------|------|------|
| $R_{\theta JA}$ | Thermal Resistance Junction-ambient | ---  | 75   | °C/W |
| $R_{\theta JC}$ | Thermal Resistance Junction-case    | ---  | 0.89 | °C/W |

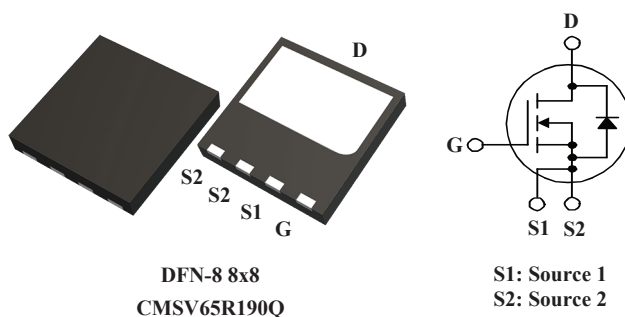
## Product Summary

| BVDSS | $R_{DS(on)}$ max. | ID  |
|-------|-------------------|-----|
| 650V  | 0.199Ω            | 20A |

## Applications

- Server and Telecom Power Supplies
- Solar Inverters
- Adaptors

## DFN-8 8x8 Pin Configuration



Electrical Characteristics ( $T_J=25^{\circ}\text{C}$  , unless otherwise noted)

| Symbol       | Parameter                         | Conditions                                    | Min. | Typ. | Max.      | Unit     |
|--------------|-----------------------------------|-----------------------------------------------|------|------|-----------|----------|
| $BV_{DSS}$   | Drain-Source Breakdown Voltage    | $V_{GS}=0V$ , $I_D=250\mu A$                  | 650  | ---  | ---       | V        |
| $R_{DS(ON)}$ | Static Drain-Source On-Resistance | $V_{GS}=10V$ , $I_D=10A$                      | ---  | 0.18 | 0.199     | $\Omega$ |
| $V_{GS(th)}$ | Gate Threshold Voltage            | $V_{GS}=V_{DS}$ , $I_D=250\mu A$              | 2    | ---  | 4         | V        |
| $I_{DSS}$    | Drain-Source Leakage Current      | $V_{DS}=600V$ , $V_{GS}=0V$                   | ---  | ---  | 1         | $\mu A$  |
|              |                                   | $V_{DS}=600V$ , $T_C=150^{\circ}\text{C}$     | ---  | 10   | ---       |          |
| $I_{GSS}$    | Gate-Source Leakage Current       | $V_{GS}=\pm 30V$ , $V_{DS}=0V$                | ---  | ---  | $\pm 100$ | nA       |
| $g_{fs}$     | Forward Transconductance          | $V_{DS}=10V$ , $I_D=10A$                      | ---  | 16   | ---       | S        |
| $R_g$        | Gate Resistance                   | $V_{DS}=0V$ , $V_{GS}=0V$ , $f=1\text{MHz}$   | ---  | 8.2  | ---       | $\Omega$ |
| $Q_g$        | Total Gate Charge                 | $I_D=20A$                                     | ---  | 36   | ---       | nC       |
| $Q_{gs}$     | Gate-Source Charge                | $V_{DS}=480V$                                 | ---  | 9    | ---       |          |
| $Q_{gd}$     | Gate-Drain Charge                 | $V_{GS}=10V$                                  | ---  | 14   | ---       |          |
| $T_{d(on)}$  | Turn-On Delay Time                | $V_{DS}=300V$                                 | ---  | 25   | ---       | ns       |
| $T_r$        | Rise Time                         | $V_{GS}=10V$                                  | ---  | 90   | ---       |          |
| $T_{d(off)}$ | Turn-Off Delay Time               | $I_D=20A$                                     | ---  | 212  | ---       |          |
| $T_f$        | Fall Time                         | $R_G=25\Omega$                                | ---  | 68   | ---       |          |
| $C_{iss}$    | Input Capacitance                 | $V_{DS}=100V$ , $V_{GS}=0V$ , $f=1\text{MHz}$ | ---  | 1430 | ---       | pF       |
| $C_{oss}$    | Output Capacitance                |                                               | ---  | 60   | ---       |          |
| $C_{rss}$    | Reverse Transfer Capacitance      |                                               | ---  | 4.3  | ---       |          |

## Diode Characteristics

| Symbol   | Parameter                 | Conditions                                         | Min. | Typ. | Max. | Unit    |
|----------|---------------------------|----------------------------------------------------|------|------|------|---------|
| $I_S$    | Continuous Source Current | $V_G=V_D=0V$ , Force Current                       | ---  | ---  | 20   | A       |
| $I_{SM}$ | Pulsed Source Current     |                                                    | ---  | ---  | 80   | A       |
| $V_{SD}$ | Diode Forward Voltage     | $V_{GS}=0V$ , $I_S=20A$ , $T_J=25^{\circ}\text{C}$ | ---  | 0.95 | 1.4  | V       |
| $t_{rr}$ | Reverse Recovery Time     | $di/dt = 100A/\mu s$                               | ---  | 347  | ---  | ns      |
| $Q_{rr}$ | Reverse Recovery Charge   | $V_{DD}=100V$ , $I_{SD}=20A$                       | ---  | 5.3  | ---  | $\mu C$ |

Note :

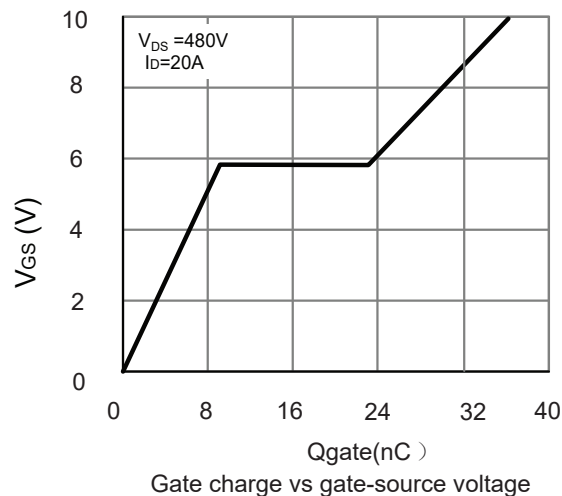
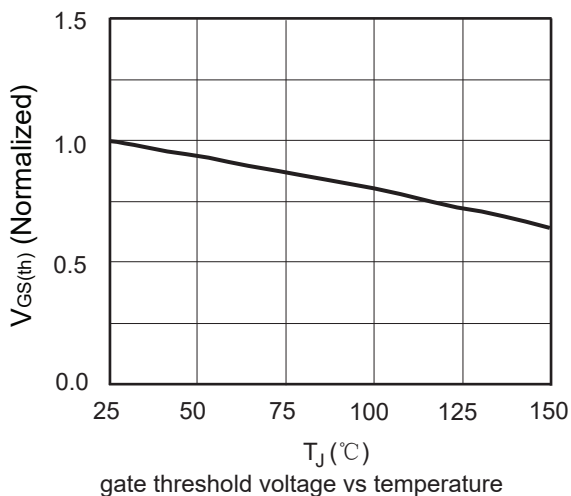
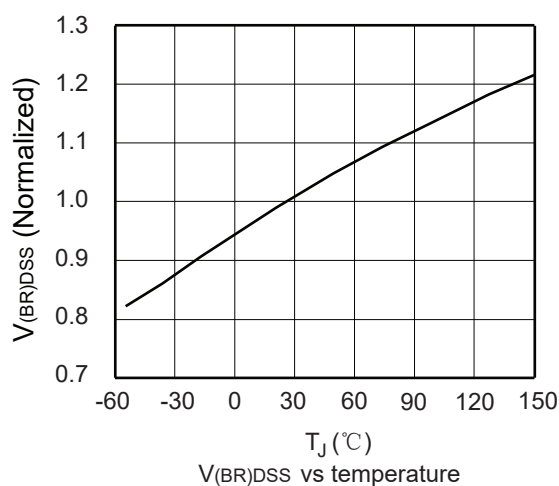
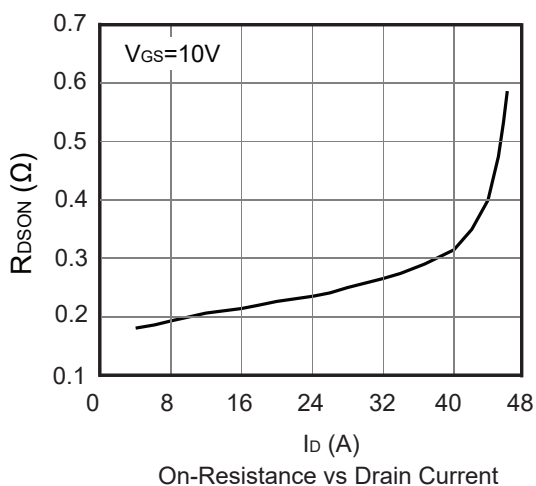
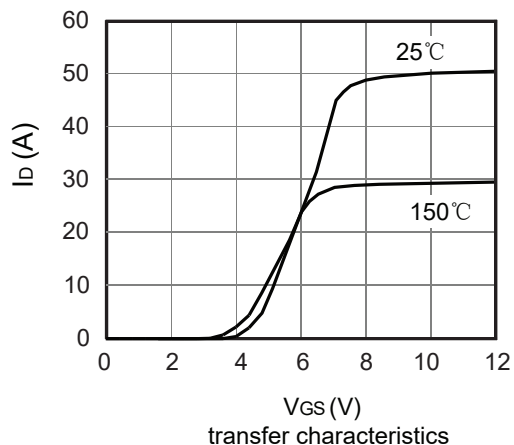
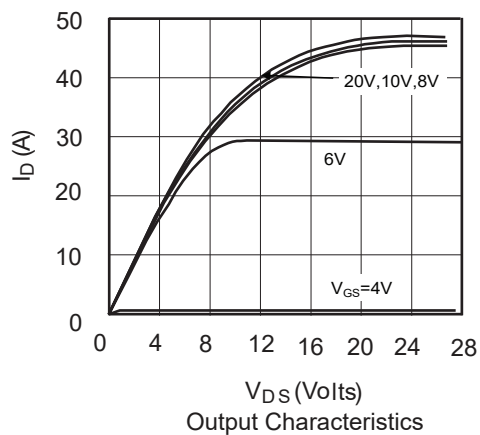
1. The EAS data shows Max. rating . The test condition is  $V_{DD}=50V$  ,  $V_{GS}=10V$  ,  $L=10mH$  ,  $I_{AS}=11A$ .

This product has been designed and qualified for the consumer market.

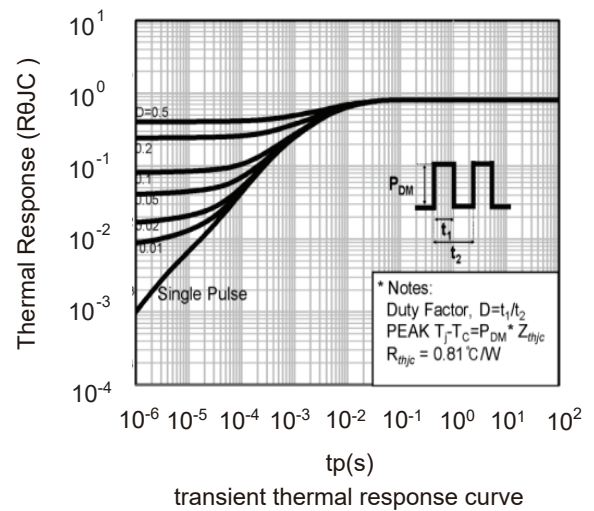
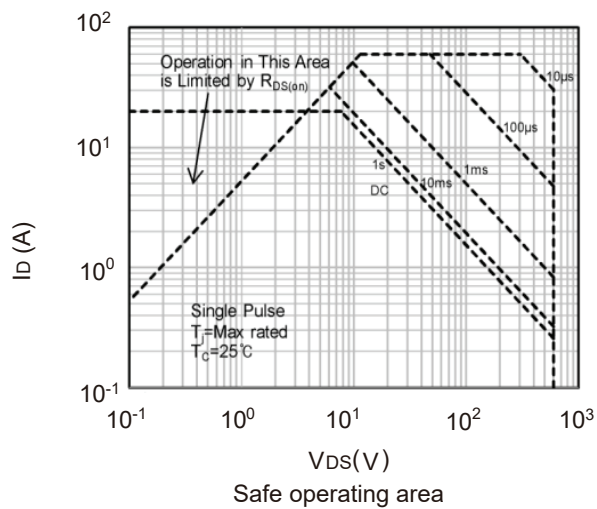
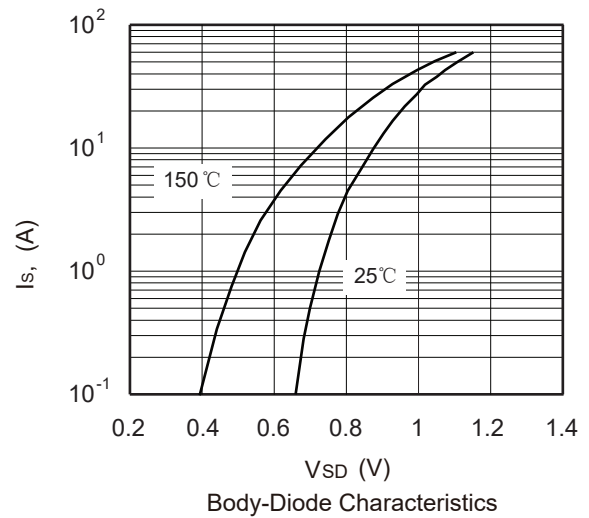
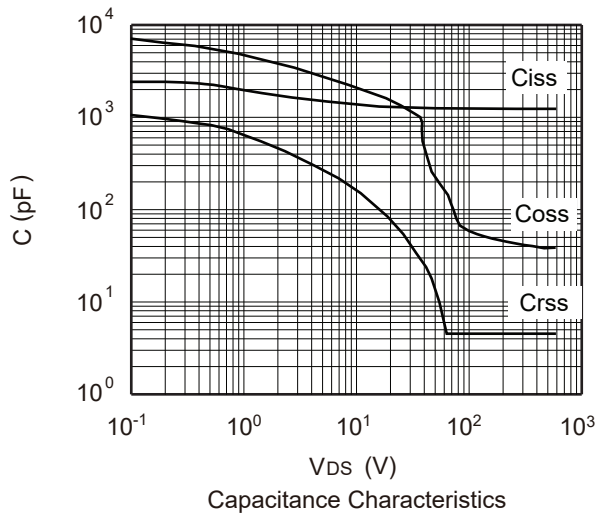
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Cmos reserves the right to improve product design ,functions and reliability without notice. Please refer to the latest version of specification.

## Typical Characteristics

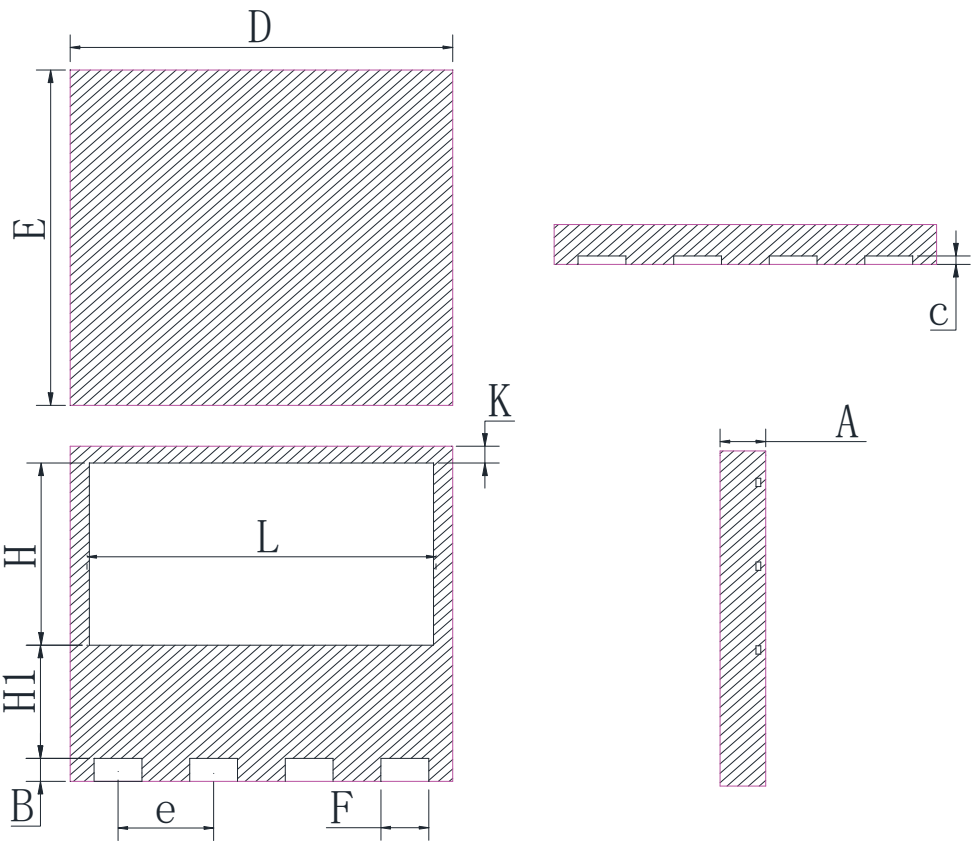


### Typical Characteristics



Package Dimension

DFN-8 8x8 Unit :mm



| Symbol | Min   | Typ   | Max   |
|--------|-------|-------|-------|
| A      | 0.90  | 0.95  | 1.00  |
| B      | 0.45  | 0.55  | 0.65  |
| C      | 0.153 | 0.203 | 0.253 |
| D      | 7.90  | 8.00  | 8.10  |
| E      | 7.90  | 8.00  | 8.10  |
| e      | 1.90  | 2.00  | 2.10  |
| F      | 0.90  | 1.00  | 1.10  |
| H      | 4.20  | 4.35  | 4.45  |
| H1     | 2.60  | 2.70  | 2.80  |
| K      | 0.30  | 0.40  | 0.50  |
| L      | 7.10  | 7.20  | 7.30  |